

NPN SILICON RF POWER TRANSISTOR

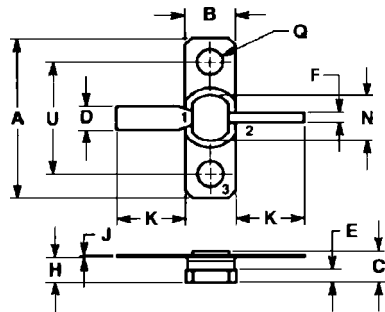
DESCRIPTION:

The **MSC81111** is Designed for Class "C" Amplifier Applications from 0.4 to 1.2 GHz, Supplied in Common Base Package.

MAXIMUM RATINGS

I_C	600 mA
V_{CB}	35 V
P_{DISS}	21.8 W @ T _C = 25 °C
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +200 °C
θ_{JC}	8 °C/W

PACKAGE STYLE HLP-1				
Dim:	Inches		Millimeters	
	Min	Max	Min	Max
A	0.790	0.810	20.07	20.6
B	0.225	0.235	5.72	5.97
C	0.144	0.180	3.66	4.58
D	0.115	0.125	2.93	3.17
E	0.055	0.065	1.40	1.65
F	0.045	0.055	1.15	1.39
H	0.115	0.135	2.93	3.42
J	0.003	0.006	0.08	0.15
K	0.225	0.275	5.72	6.98
N	0.220	0.240	5.59	6.09
Q	0.125	0.135	3.18	3.42
U	0.552	0.572	14.03	14.5



1 = Emitter 2 = Collector
3 = Base

CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CER}	I _C = 5.0 mA R _{BE} = 10Ω	45			V
BV_{CBO}	I _C = 1.0 mA	45			V
I_{CBO}	V _{CB} = 28 V			1.0	mA
BV_{EBO}	I _E = 1.0 mA	3.5			V
h_{FE}	V _{CE} = 5.0 V I _C = 200 mA	15		120	---
C_{OB}	V _{CB} = 28 V f = 1.0 MHz			6.5	pF
P_{out}	V _{CC} = 28 V P _{in} = 500 mW f = 1.0 GHz	5.0	6.6		W
η_C		50	52		%
G_P		10	11.2		dB